

IN THE CLAIMS:

Please amend the claims as follows:

1. – 7. (Cancelled)

8.(Currently Amended) A method of etching and cleaning a TiW alloy layer comprising:

providing a substrate comprising an exposed TiW alloy layer;

etching the TiW alloy by a method which results in formation of etching residue;

contacting the substrate with a TiW-selective composition comprising water and between about 7.5% to about 15% by weight of periodic acid, wherein the composition is effective in removing a TiW alloy and removing residues of etching of TiW alloy while removing a relatively small amount of Al, Cu, or an AlCu alloy, and wherein the pH of the composition is less than 7 ~~the composition of claim 1~~ for a time and at a temperature sufficient to cause the composition to remove at least a portion of the TiW alloy and substantially all of the etching residue from the substrate; and
rinsing the substrate.

9. (Currently Amended) The method of claim 8, wherein the substrate further comprises an exposed AlCu alloy, wherein by removing a relatively small amount of Al, Cu, or an AlCu alloy means the specificity of removal of TiW to AlCu, in terms of etch rate, is at least about 3.

10.(Previously Presented) The method of claim 9, wherein the substrate further comprises an exposed AlCu alloy, wherein the specificity of removal of TiW to AlCu, in terms of etch rate, is at least about 5.

11. (Currently Amended) The method of claim 10, wherein the substrate further comprises an exposed AlCu alloy, wherein the specificity of removal of TiW to AlCu, in terms of etch rate, is at least about 7.

12. (original) The method of claim 8, wherein the temperature at which the solution is used ranges from about 20°C to about 100°C.

13. (original) The method of claim 8, wherein the temperature at which the solution is used ranges from about 30°C to about 40°C.

14. (original) A method of etching and cleaning TiW layer comprising:
providing a substrate comprising a TiW alloy layer and etching residues from prior etching of the TiW layer;
contacting the substrate with a solution containing hydrogen peroxide for a time and at a temperature sufficient to cause the solution to substantially remove exposed TiW alloy;
contacting the substrate with the composition of claim 1 for a time and at a temperature sufficient to substantially remove the residues from the substrate; and
rinsing the substrate.

15. (original) The method of claim 14, wherein the temperature at which the solution is used ranges from about 20°C to about 100°C.

16. (original) The method of claim 15, wherein the temperature at which the solution is used ranges from about 30°C to about 40°C.

17.(New) The method of claim 15, wherein the composition is substantially free of hydrofluoric acid.

18.(New) The method of claim 15, wherein the composition contains periodic acid in an amount from about 7.5% to about 15% by weight of the composition.

19.(New) The method of claim 15, wherein the composition contains periodic acid in an amount from about 8% to about 12% by weight of the composition, and wherein the pH of the composition is less than about 4.